

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S15	855	(257/338 or 257/351).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 09:43
S16	747	(257/338 or 257/351).ccls. and @ad<"20030815"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 10:36
S12	59	(257/368 or 257/369).ccls. and (((lattice near3 constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 10:38
S19	3024	(257/368 or 257/369).ccls. and @ad<"20030815"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 10:48
S21	190	(257/376).ccls. and @ad<"20030815"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 10:55
S23	512	(257/616 or 257/617).ccls. and @ad<"20030815"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/11 10:55
S20	159	(257/368 or 257/369).ccls. and (((lattice) or strain\$3) same (silicon or si or germanium or ge or carbon or c)) and @ad<"20030815"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 10:56
S24	247	(257/616 or 257/617).ccls. and (((lattice) or strain\$3) same (silicon or si or germanium or ge or carbon or c)) and @ad<"20030815"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 10:56
S2	1897	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice near constant) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 17:17

S25	5539	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice) or strain\$3) with (silicon or si or germanium or ge or carbon or c))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 17:17
S26	4396	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice) or strain\$3) with (silicon or si or germanium or ge or carbon or c)) and @ad<"20030815"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 17:19
S27	3506	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice) or strain\$3) with (silicon or si and (germanium or ge) and (carbon or c))) and @ad<"20030815"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 17:21
S28	1314	semiconductor and (CMOS or complementary or (NMOS same PMOS)) and (((lattice adj constant) or strain\$3) with (silicon or si and (germanium or ge) and (carbon or c))) and @ad<"20030815"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/11 17:21